

20V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ max	I_D max $T_A = 25^\circ\text{C}$ (Note 3)
20V	20m Ω @ $V_{GS} = 4.5\text{V}$	9.8A
	28m Ω @ $V_{GS} = 2.5\text{V}$	8.3A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

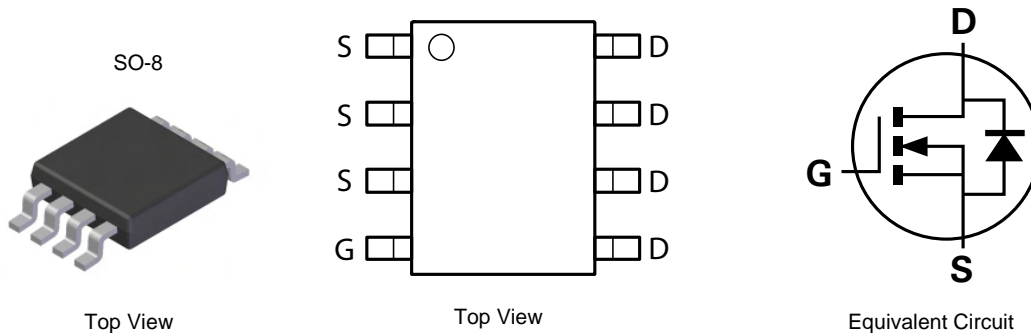
- Battery charging
- Power management functions
- DC-DC converters
- Portable power adaptors

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Lead Free/RoHS Compliant (Note 1)**
- **Halogen and Antimony Free. "Green" Device (Note 1)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish – Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.074 grams (approximate)

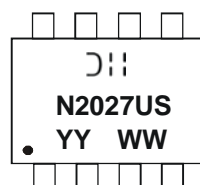


Ordering Information (Note 1)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMN2027USS-13	N2027US	13	12	2,500

Notes: 1. No purposefully added lead. Diodes Inc.'s "Green" policy and packaging details can be found on our website at <http://www.diodes.com>

Marking Information



⏏ = Manufacturer's Marking
 N2027US = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Year (ex: 10 = 2010)
 WW = Week (01 - 53)

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

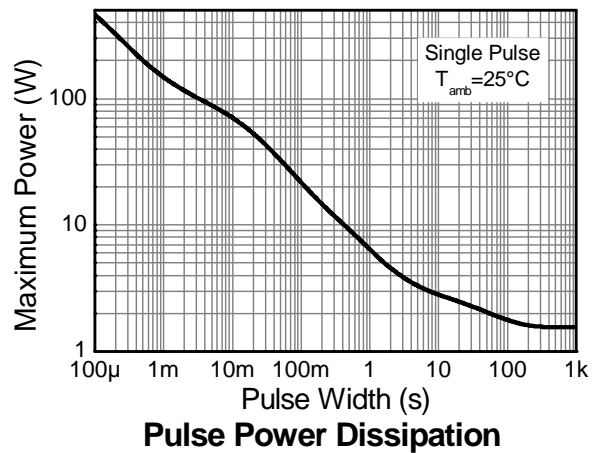
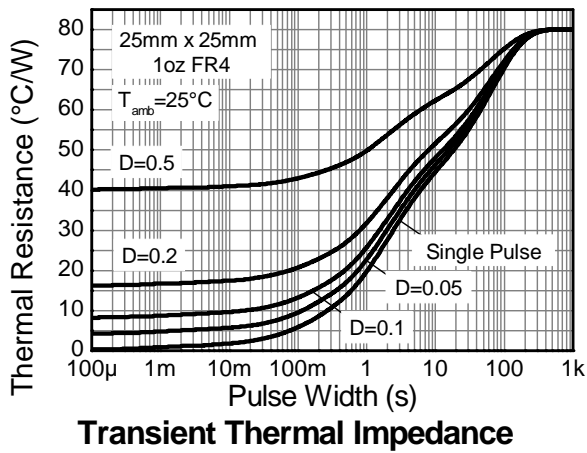
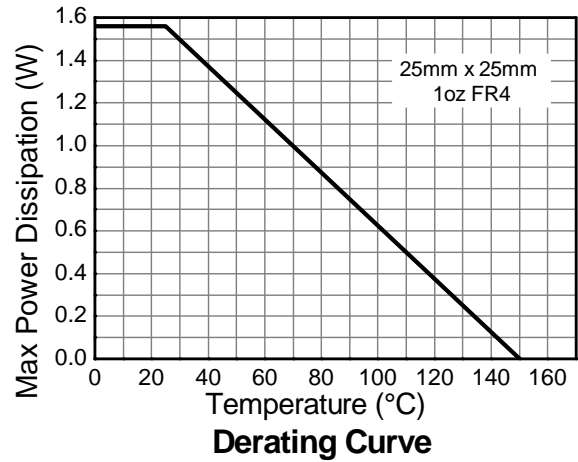
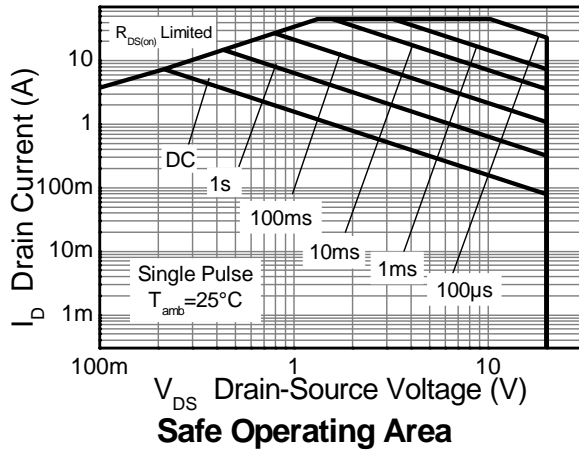
Characteristic			Symbol	Value	Unit
Drain-Source voltage			V_{DSS}	20	V
Gate-Source voltage			V_{GS}	± 12	
Continuous Drain current	$V_{GS} = 4.5\text{V}$	(Note 3)	I_D	9.8	A
		$T_A = 70^\circ\text{C}$ (Note 3)		7.9	
		(Note 2)		7.3	
Pulsed Drain current	$V_{GS} = 4.5\text{V}$	(Note 4)	I_{DM}	45.0	
Continuous Source current (Body diode)			(Note 3)	I_S	
Pulsed Source current (Body diode)			(Note 4)	I_{SM}	45.0

Thermal Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic		Symbol	Value	Unit
Power dissipation	(Note 2)	P_D	1.56	W
			12.5	
Linear derating factor	(Note 3)		2.81	
Thermal Resistance, Junction to Ambient	(Note 2)	$R_{\theta JA}$	80.0	$^\circ\text{C/W}$
	(Note 3)		44.5	
Thermal Resistance, Junction to Lead	(Note 5)	$R_{\theta JL}$	37.0	
Operating and storage temperature range		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

- Notes:
- For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 - Same as note (2), except the device is measured at $t \leq 10$ sec.
 - Same as note (2), except the device is pulsed with $D = 0.02$ and pulse width 300 μs .
 - Thermal resistance from junction to solder-point (at the end of the drain lead).

Thermal Characteristics



Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	20	-	-	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1.0	μA	V _{DS} = 20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	V _{GS} = ±12V, V _{DS} = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(th)}	0.6	1.0	1.3	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance (Note 6)	R _{DS(on)}	-	11	20	mΩ	V _{GS} = 4.5V, I _D = 9.4A
			15	28		V _{GS} = 2.5V, I _D = 8.3A
Forward Transfer Admittance (Note 6 & 7)	Y _{fs}	-	16	-	S	V _{DS} = 5V, I _D = 9.4A
Diode Forward Voltage (Note 6)	V _{SD}	-	0.7	1.3	V	V _{GS} = 0V, I _S = 1.3A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iSS}	-	1000	-	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oSS}	-	166	-		
Reverse Transfer Capacitance	C _{rSS}	-	158	-		
Gate Resistance	R _g	-	1.51	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (Note 8)	Q _g	-	7.0	-	nC	V _{GS} = 2.5V V _{DS} = 10V I _D = 9.4A
Total Gate Charge (Note 8)	Q _g	-	11.6	-		
Gate-Source Charge (Note 8)	Q _{gs}	-	2.7	-		
Gate-Drain Charge (Note 8)	Q _{gd}	-	3.4	-		
Turn-On Delay Time (Note 8)	t _{D(on)}	-	11.67	-	ns	V _{GS} = 4.5V, V _{DS} = 10V, R _G = 6Ω, I _D = 1A
Turn-On Rise Time (Note 8)	t _r	-	12.49	-		
Turn-Off Delay Time (Note 8)	t _{D(off)}	-	35.89	-		
Turn-Off Fall Time (Note 8)	t _f	-	12.33	-		

- Notes:
6. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%
 7. For design aid only, not subject to production testing.
 8. Switching characteristics are independent of operating junction temperatures.

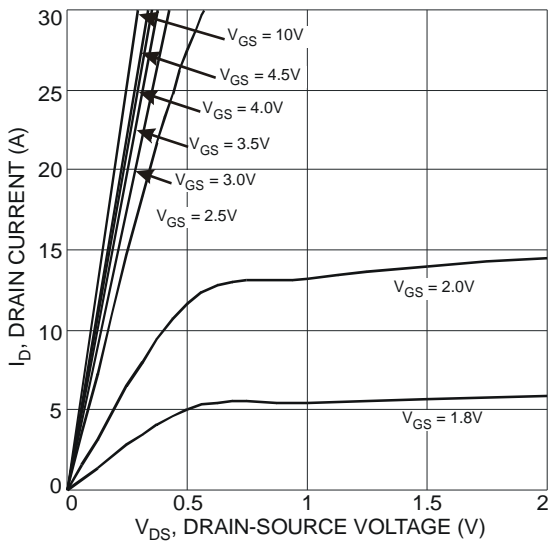


Fig. 1 Typical Output Characteristic

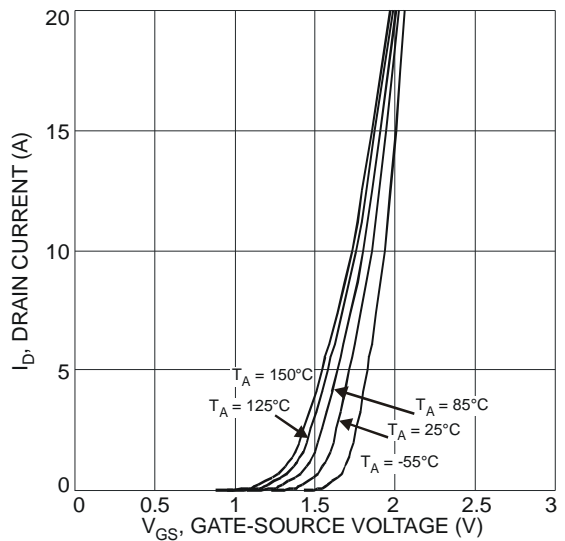


Fig. 2 Typical Transfer Characteristic

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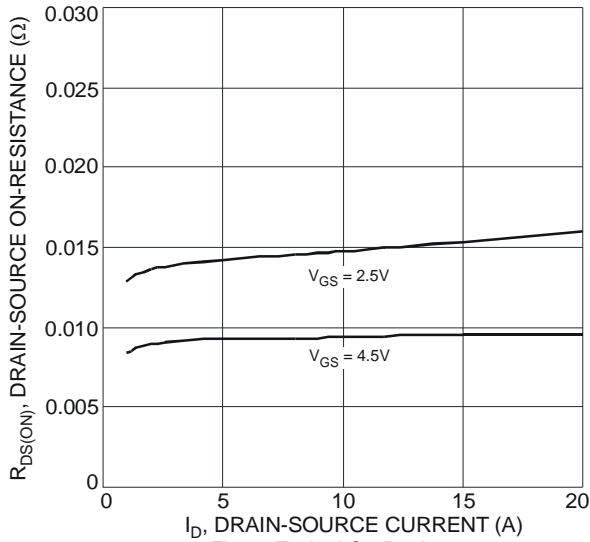


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

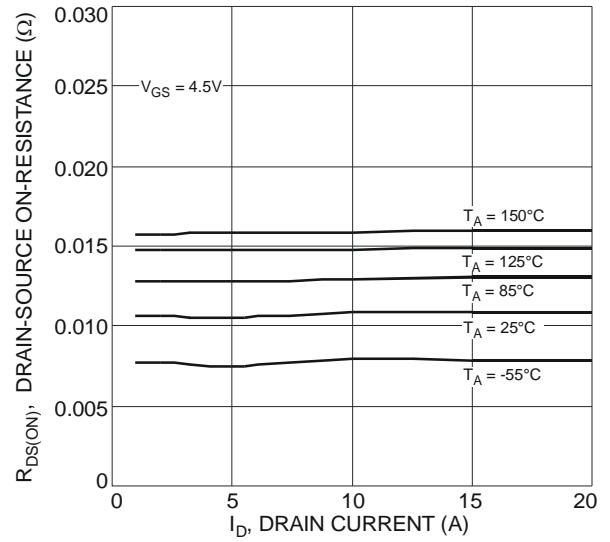


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

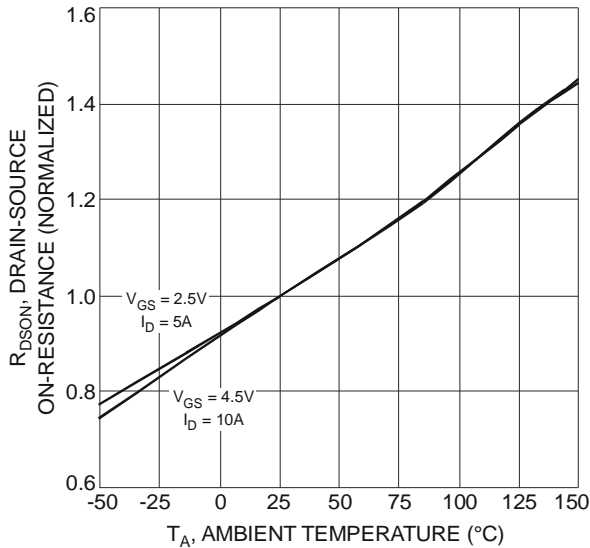


Fig. 5 On-Resistance Variation with Temperature

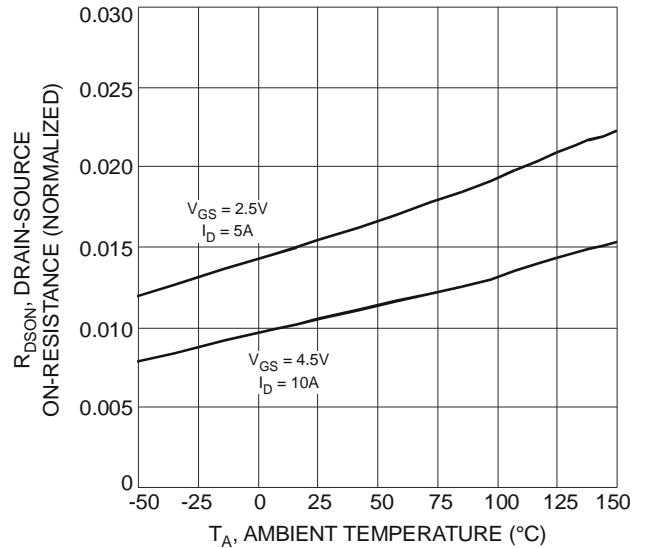


Fig. 6 On-Resistance Variation with Temperature

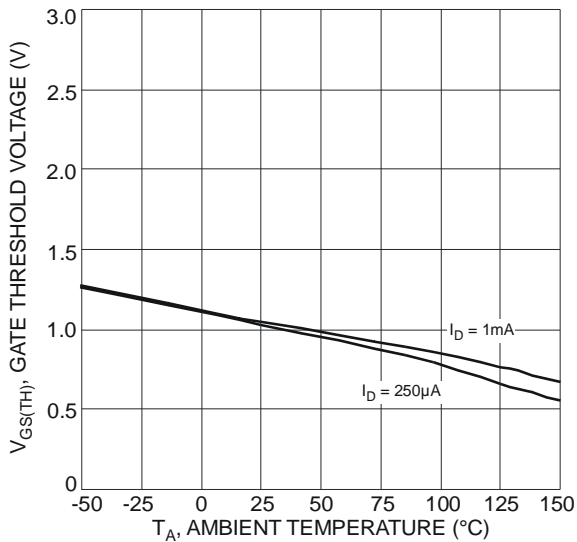


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

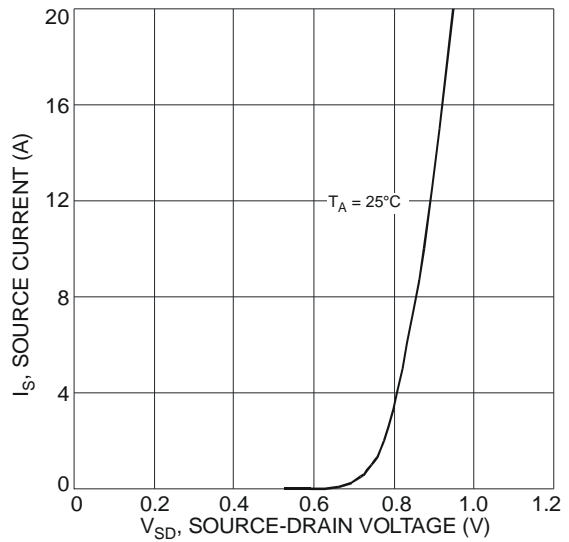


Fig. 8 Diode Forward Voltage vs. Current

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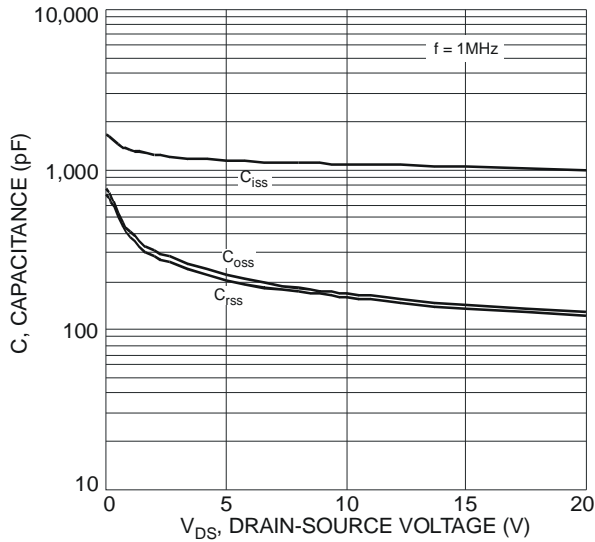


Fig. 9 Typical Total Capacitance

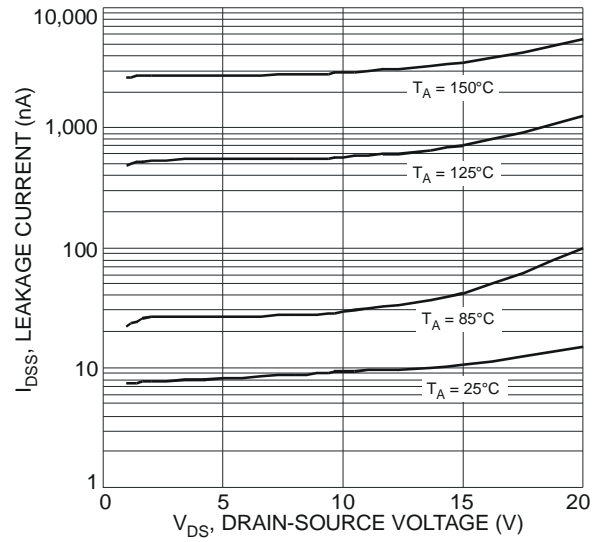


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

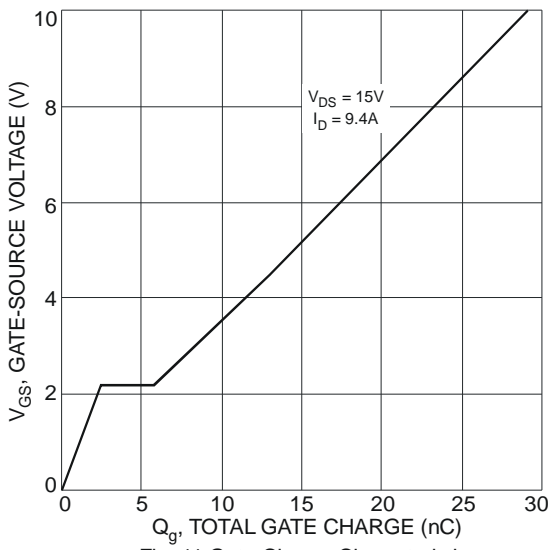
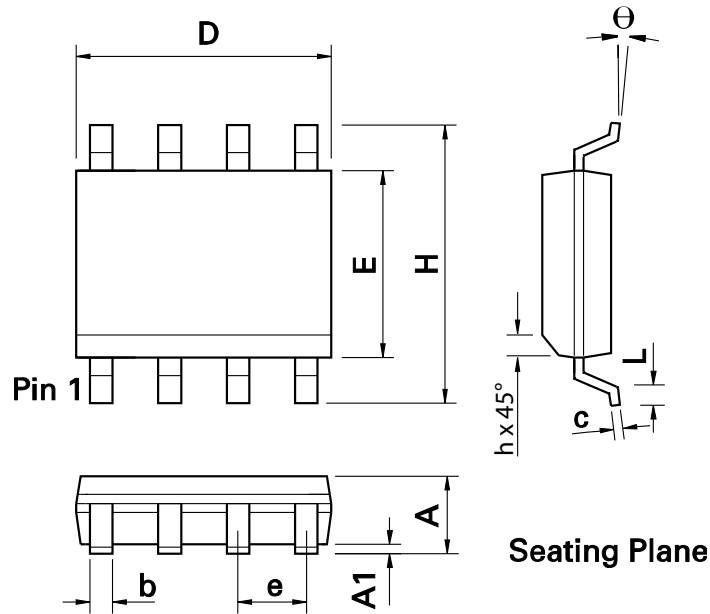


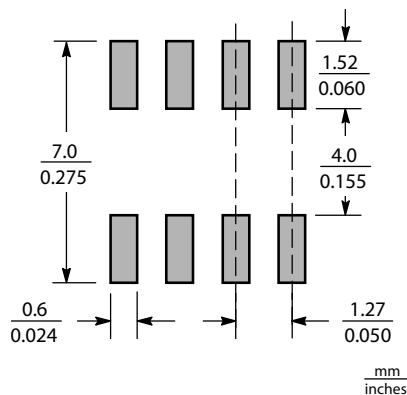
Fig. 11 Gate-Charge Characteristics

Package Outline Dimensions



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.053	0.069	1.35	1.75	e	0.050 BSC		1.27 BSC	
A1	0.004	0.010	0.10	0.25	b	0.013	0.020	0.33	0.51
D	0.189	0.197	4.80	5.00	c	0.008	0.010	0.19	0.25
H	0.228	0.244	5.80	6.20	θ	0°	8°	0°	8°
E	0.150	0.157	3.80	4.00	h	0.010	0.020	0.25	0.50
L	0.016	0.050	0.40	1.27	-	-	-	-	-

Suggested Pad Layout



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